Product data sheet

1. General description

PNP low V_{CEsat} transistor in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4350Z-Q

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- High energy efficiency due to less heat generation
- Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- DC/DC converters
- · Supply line switching
- · Battery charger
- · LED backlighting
- Linear voltage regulation (LDO)
- Driver in low supply voltage applications, e.g. lamps, LEDs
- Inductive load driver (for example relays, buzzers, motors)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base		-	-	-50	V
Ic	collector current			-	-	-3	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	-5	Α
R _{CEsat}	collector-emitter saturation resistance	I _C = -2 A; I _B = -200 mA; T _{amb} = 25 °C	[1]	-	120	150	mΩ

[1] Pulsed test: $t_p \le 300 \ \mu s; \ \delta \le 0.02$



50 V, 3 A PNP low VCEsat transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	С
2	С	collector		5
3	E	emitter		B—
4	С	collector	☐1 ☐2 ☐3 SC-73 (SOT223)	E sym132

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBSS5350Z-Q		plastic, surface-mounted package with increased heatsink; 4 leads; 2.3 mm pitch; 6.5 mm x 3.5 mm x 1.65 mm body	SOT223

7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS5350Z-Q	PB5350

8. Limiting values

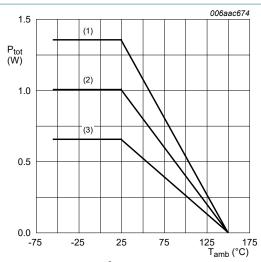
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-60	V
V _{CEO}	collector-emitter voltage	open base		-	-50	V
V _{EBO}	emitter-base voltage	open collector		-	-6	V
I _C	collector current			-	-3	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-5	А
I _{BM}	peak base current			-	-1	А
P _{tot}	total power dissipation		[1]	-	0.65	W
			[2]	-	1	W
			[3] [4]	-	1.35	W
			[5]	-	2	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), 35 µm single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, 35 µm single-sided copper, tin-plated, mounting pad for collector 1 cm². Device mounted on an FR4 PCB, 35 µm single-sided copper, tin-plated, mounting pad for collector 6 cm².
- Device mounted on an FR4 PCB, 70 µm single-sided copper, tin-plated, mounting pad for collector 1 cm².
- Device mounted on an FR4 PCB, 70 µm single-sided copper, tin-plated, mounting pad for collector 6 cm².

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- (1) FR4 PCB, mounting pad for collector 6 cm²
- (2) FR4 PCB, mounting pad for collector 1 cm²
- (3) FR4 PCB, standard footprint

Power derating curves Fig. 1.

9. Thermal characteristics

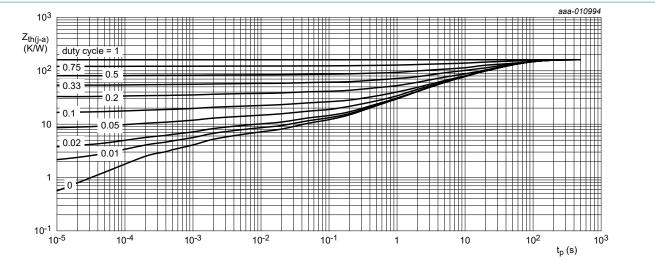
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	-	192	K/W
	junction to ambient		[2]	-	-	125	K/W
			[3] [4]	-	-	92	K/W
			[5]	-	-	62.5	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	16	K/W

- Device mounted on an FR4 PCB, 35 μ m single-sided copper, tin-plated and standard footprint. Device mounted on an FR4 PCB, 35 μ m single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3]
- Device mounted on an FR4 PCB, 35 µm single-sided copper, tin-plated, mounting pad for collector 6 cm². Device mounted on an FR4 PCB, 70 µm single-sided copper, tin-plated, mounting pad for collector 1 cm². Device mounted on an FR4 PCB, 70 µm single-sided copper, tin-plated, mounting pad for collector 6 cm².

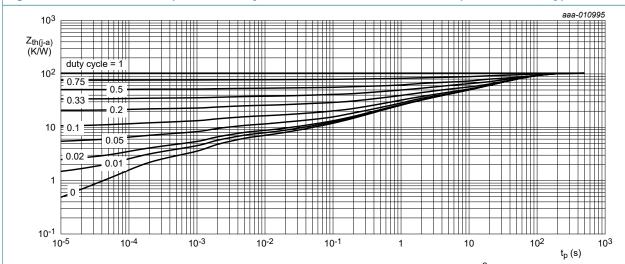
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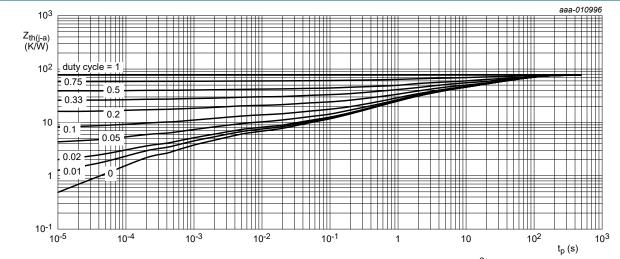
FR4 PCB, 35 µm single-sided copper, tin-plated and standard footprint.

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, 35 µm single-sided copper, tin-plated, mounting pad for collector 1 cm².

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, 35 µm single-sided copper, tin-plated, mounting pad for collector 6 cm².

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

 T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{(BR)CBO}	collector-base breakdown voltage	I _C = -100 μA; I _E = 0 A		-60	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	I _C = -10 mA; I _B = 0 A		-50	-	-	V
V _{(BR)EBO}	emitter-base breakdown voltage (collector open)	I _E = -100 μA; I _C = 0 A		-6	-	-	V
I _{СВО}	collector-base cut-off	V _{CB} = -50 V; I _E = 0 A		-	-	-100	nA
CBC	current	V _{CB} = -50 V; I _E = 0 A; T _j = 150 °C		-	-	-50	μΑ
I _{ЕВО}	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0 A		-	-	-100	nA
h _{FE}	DC current gain	V _{CE} = -2 V; I _C = -500 mA		200	-	-	
		V _{CE} = -2 V; I _C = -1 A	[1]	200	-	-	
		V _{CE} = -2 V; I _C = -2 A	[1]	100	-	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = -500 mA; I _B = -50 mA		-	-	-100	mV
		I _C = -1 A; I _B = -50 mA		-	-	-180	mV
		I _C = -2 A; I _B = -200 mA	[1]	-	-	-300	mV
R _{CEsat}	collector-emitter saturation resistance	I _C = -2 A; I _B = -200 mA; T _{amb} = 25 °C	[1]	-	120	150	mΩ
V _{BEsat}	base-emitter saturation voltage	I _C = -2 A; I _B = -200 mA	[1]	-	-	-1.2	V
V_{BEon}	base-emitter turn-on voltage	V _{CE} = -2 V; I _C = -1 A; T _{amb} = 25 °C	[1]	-	-	-1.1	V
T	transition frequency	$V_{CE} = -5 \text{ V}; I_{C} = -100 \text{ mA}; f = 100 \text{ MHz}$		100	-	-	MHz
C _c	collector capacitance	V_{CB} = -10 V; I_E = 0 A; i_e = 0 A; f = 1 MHz		-	-	40	pF

^[1] Pulsed test: $t_p \le 300 \ \mu s; \ \delta \le 0.02$

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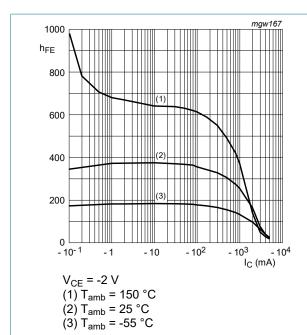


Fig. 5. DC current gain as a function of collector current; typical values

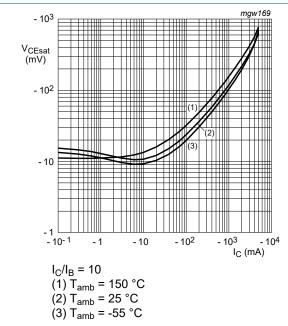
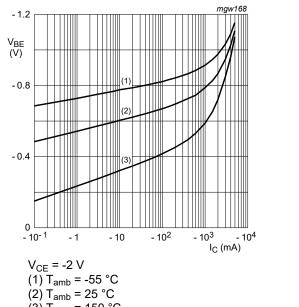
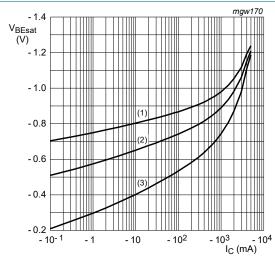


Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values



 $(3) T_{amb} = 150 °C$

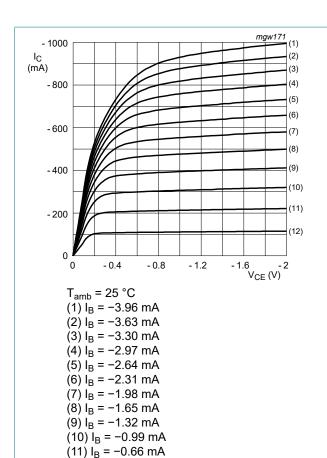
Fig. 6. Base-emitter voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 10$ (1) $T_{amb} = -55 \, ^{\circ}C$ (2) $T_{amb} = 25 \, ^{\circ}C$ (3) $T_{amb} = 150 \, ^{\circ}C$

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

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(12) I_B = −0.33 mA
Fig. 9. Collector current as a function of collector-emitter voltage; typical values

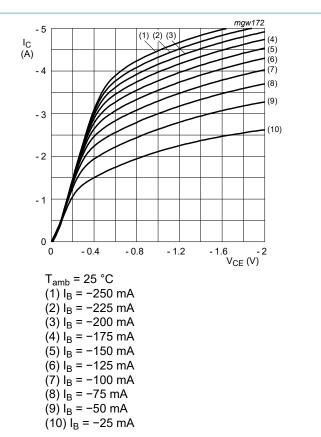
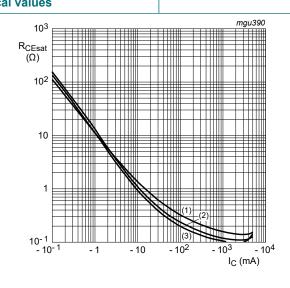


Fig. 10. Collector current as a function of collectoremitter voltage; typical values



 $I_C/I_B = 20$ (1) $T_{amb} = 150 \,^{\circ}C$ (2) $T_{amb} = 25 \,^{\circ}C$

(3) $T_{amb} = -55$ °C

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

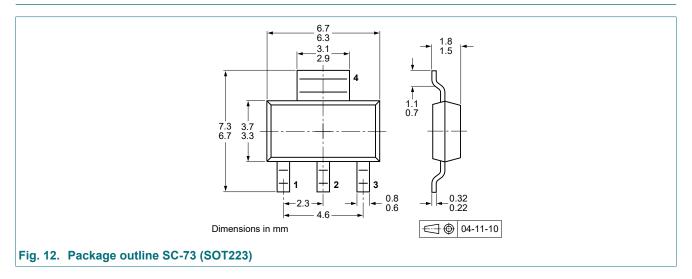
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11. Test information

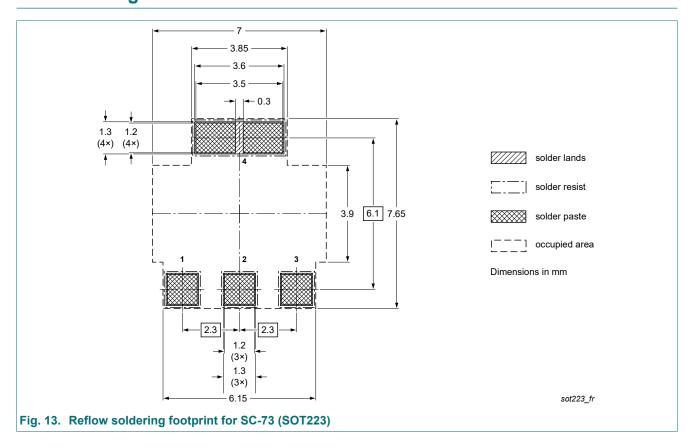
Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

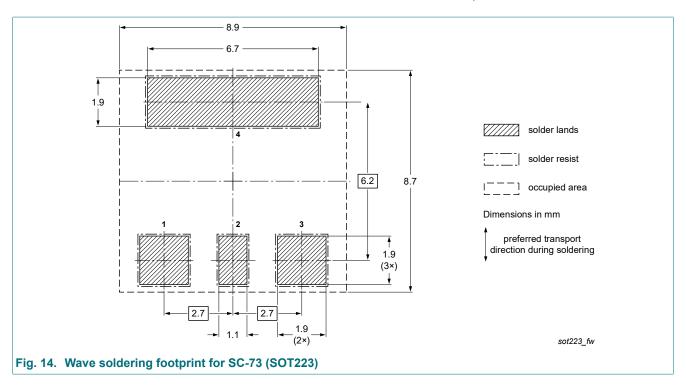
12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5350Z-Q v.1	20220831	Product data sheet	-	-

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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